New Jersey Semi-Conductor Products, Inc.

20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.

TELEPHONE: (973) 376-2922 (212) 227-6005 FAX: (973) 376-8960

TIC126M

APPLICATIONS

- 12A contimunous on-state current
- 100A surge-current

Thyristors

- · Glass passivated
- Max I_{GT} of 20mA

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	600	V
V _{RRM}	Repetitive peak reverse voltage	600	V
I _{T(AV)}	On-state current Tc=80℃	7.5	A
I _{T(RMS)}	RMS on-state current Tc=80°C	12	A
I _{TM}	Surge peak on-state current	100	A
P _{GM}	Peak gate power P _W ≤300 µ s	5	w
P _{G(AV)}	Average gate power	1	W
Tj	Operating Junction temperature	110	°C
T _{stg}	Storage temperature	-40 ~+125	°C
R _{th(j-c)}	Thermal resistance, junction to case	2.4	°C/W
R _{th(j−a)}	Thermal resistance, junction to ambient	62.5	°C /W



ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I _{RRM}	Repetitive peak reverse current	V _{RM} =V _{RRM} , Tj=110℃			2.0	mA
I _{DRM}	Repetitive peak off-state current	V _{RM} =V _{RRM} , Tj=110℃			2.0	mA
V_{TM}	On-state voltage	I _{TM} = 12A			1.4	V
I _{GT}	Gate-trigger current	V _{AA} =6V; R _L =100 Ω			20	mA
V _{GT}	Gate-trigger voltage	V _{AA} =6V; R _L =100 Ω			1.5	V
I _H	Holding current	V _{AA} =6V; R _{GK} =1k Ω ,I _T =100mA			40	mA

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors